

ABSTRACT OF THE DISCLOSURE

Disclosed is a semiconductor device including: a semiconductor substrate; a plurality of diffusion layer patterns
5 formed on the semiconductor substrate; an insulation film formed between the plural diffusion layer patterns on the semiconductor substrate; and a through plug formed to be partly surrounded by the insulation film without being in contact with the plural diffusion layer patterns and to pass through the insulation film and the
10 semiconductor substrate. Further disclosed is a semiconductor device including: a semiconductor substrate; a plurality of diffusion layer patterns formed on the semiconductor substrate; an insulation film formed between the plural diffusion layer patterns on the semiconductor substrate; and a through plug formed to be
15 partly surrounded by the diffusion layer pattern without being in contact with the insulation film and to pass through the diffusion layer pattern and the semiconductor substrate.